Tom onaga-Luttinger liquid with reservoirs in a multi-term inal geometry.

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We propose a form alism which uses boundary conditions imposed on the Luttinger liquid (LL) to describe the transport properties of a LL coupled to reservoirs. The various boundary conditions completely determine linear transport in the joint system reservoirs+ LL. As an illustration we consider an exactly solvablem icroscopic model in a multi-term inalgeometry for which such boundary conditions can be explicitly derived; in this model the Landauer-Buttiker form alism fails: if it were valid, the relation between the conductance matrix elements and the rejection and transmission coeficients could yield negative probabilities. We then apply our form alism to a discussion of shot noise through an impurity in a LL connected to two reservoirs.

I. IN TRODUCTION

For Ferm i liquids coupled to many reservoir leads linear transport properties can be described by the Landauer-Buttiker form alism whose key idea is to relate transport properties of each single electron at the Ferm i level to some transm ission and rejection probabilities that characterize the scattering properties of electrons $^{\!1;2}$. The Landauer-Buttiker formalism states that the conductance matrix elements G_{np} dened for each conducting channel by $i_n= {}_p G_{np} V_p$ (where i_n and V_p are respectively the current injected by reservoir n and the voltage of reservoir p) are related to the transm ission (T_{np}) and rejection (R_n) probabilities of single electron:

$$G_{nn} = \frac{e^2}{h} (1 R_n)$$
 (1)

$$G_{np} = \frac{e^2}{h} T_{np}$$
: (2)

Therefore: (i) $G_{nn} > 0$ and $G_{np} < 0$ and both are bounded by $e^2 = h$; (ii) in the absence of any backscattering G_{nn} has a nite universal value $G_0 = e^2 = h$ which leads in a two-term inalgeom etry to the so-called universal contact resistance that rejects the (inelastic) relaxation process of each electron that leaves the sample and enters a given reservoir.

For strongly correlated electronic systems such as the Luttinger Liquid (LL) the single particle scattering matrix approach essential to the Landauer-Buttiker form alism becomes inadequate because in a LL the single-particle Green function has no quasiparticle pole which means that electrons do not propagate³.

Nevertheless, the Landauer-Buttiker formalism has been widely used to interpret recent two and multiterm inal linear transport measurements 4 on physical systems that are believed to be good examples of LL 7,8 . More precisely several experiments on quantum wires fabricated by cleaved edge overgrowth found two-term inal conductance plateaux at nonuniversal values: G = 0.8, 0.85, 0.95 and as low as 0.45 in units of the quantum of conductance G $_0$ (per channel) 7 . In Ref. 5 results for a three term inal geometry are also reported and

show that R $_{\rm n}$ \in 0 if interpreted in the Landauer-Buttiker frame. A ssum ing then that electrons in the wire are non-interacting these values can be understood by invoking some backscattering due to the coupling of the ballistic wire to the two-dimensional reservoirs 5 . Similarly individual single wall carbon nanotubes were found with either a two-term inal conductance $G = G_0^6$ but also with $G = 0.5 = 0.66_0^9$.

If one believes that quantum wires and carbon nanotubes constitute realizations of the LL the interpretation of these non universal ohm ic conductance plateaux poses a serious problem in two respects: (i) if the smaller conductances are interpreted as resulting from some backscattering (in agreement with a Landauer-Buttiker interpretation) then this is contradictory to the expectation that in a LL backscattering should lead to power law (non-ohmic) corrections; (ii) moreover in the framework of the LL theory several earlier theoretical papers found that the two-term inal conductance of a LL should be una ected by the interactions and stick to a universal value G_0 yielding the same contact resistance as in non-interacting system s^{10} .

A ctually a theoretical analysis of the transport properties of a LL in a multi-term inalgeom etry has not really been developped.

In this paper we develop a form alism to describe the linear transport properties of a LL coupled to an arbitrary number of electrodes, which play the role of charge reservoirs for the LL. Instead of a full-edged microscopic approach which is obviously unassailable we propose a form alism in which the coupling of a LL to reservoirs is taken into account by considering a LL subjected to boundary conditions. Our approach generalizes several earlier papers which take a similar stand for the modelling of a coupled system $^{11}\{^{15}$.

Our basic idea is as follows: (i) we observe that in a LL a chiral decoupling occurs, i.e. each chirality is independent of the other and is responsible for the transport of current in one direction, and therefore the transport properties are completely specified by the associated chiral chemical potentials. (ii) Imposing linear relations to the terminal voltages determines the values of these chirals.

ral potentials: each set of relation can therefore be seen as a set of boundary conditions in posed on the LL.W e consider that each set of boundary conditions characterizes some kind of coupling of the electrodes to the LL. In other words as far as the transport properties are concerned we view a given set of boundary conditions as corresponding to a universality class for the total system consisting of both the LL and the electrodes. That form alism is explained in section 2.

To substantiate our views we consider in section 3 an exactly solvable model of strongly correlated ferm ions coupled to an arbitrary number of term in als and for which such boundary conditions can be derived explicitly. We not that in the toy model of section 3 the signs of the conductancem atrix elements are not xed: if we were to de ne rejection and transmission coecients R $_{\rm n}$ and $T_{\rm np}$ through equations (1,2) we would get negative probabilities. That the probabilistic view of transport given by the Landauer-Buttiker formalism fails is hardly surprising: transport in a LL is not ensured by electrons (or Landau quasiparticles) but by fractional excitations akin to those of the Fractional Quantum Hall Eject (FQHE) 16 .

In section 4 we specialize to the two-term inal geom etry. We show that the boundary conditions are equivalent in that geom etry to specifying contact resistances at the source and the drain. We explain how our formalism allows us to classify earlier theories: theories yield distinct conductances because they belong to dierent universality classes and correspond to distinct boundary conditions. We then consider a LL with an impurity which provides some backscattering within the system but not at the two contacts. We then discuss implications of our formalism in section 5 for the various theories of shot noise through a single impurity in a LL.

II. BOUNDARY CONDITIONS IN A MULTI-TERM IN ALGEOMETRY.

 ${\tt A}$. C hiral chem ical potentials for the LL .

W e consider the standard LL ham iltonian density:

$$H = h \frac{u}{2} K^{-1} (\theta_x)^2 + K^{-2}$$
 (3)

where we have introduced the standard phase \underline{eld} related to the electron density by: $(x;t) = \mathbb{Q}_x = \underline{l}$, and its conjugate canonicalm omentum . We also introduce the chiral densities:

$$=\frac{1}{2^{p}}=(0_{x} K)$$
: (4)

It is easy to check that these densities are indeed chiral and to show that they are related to the densities of electrons at the right and left Ferm ipoints by:

$$^{+} = Q \left[K \right] \quad \stackrel{0}{\stackrel{+}{\scriptstyle 0}} \quad ; \tag{5}$$

where:

In term s of these chiral variables the LL ham iltonian is completely decoupled into two chiral ham iltonians. Current will then be induced in the LL by adding conjugate variables to H:

$$H = + + (7)$$

which de nes chiral chem ical potentials; as usual when de ning chem ical potentials they correspond to the energy needed for the creation of $_R$ unit particle of a given chirality within the LL (Q = dx = 1). They are not de ned as the reservoir chem ical potentials. M inimization of the ham iltonian leads easily to the relation:

$$I = \frac{Ke}{h} (_{+}) :$$
 (8)

Therefore the two-term inal conductance of a LL as measured against these chiral chemical potentials is:

$$G_K = \frac{Ie}{h} = K \frac{e^2}{h}$$
 (9)

Ii is crucial to realize that the experim entally measured conductance $G_{2t} = \frac{Ie}{s}$ and G_K need not be identical. The chiral chem ical potentials (associated with the quasiparticles driving the current in the LL) will indeed usually dier from the reservoir chemical potentials.

B.Boundary conditions.

We now consider N term inals at respective voltages V_n . The geom etry is indi erent and is either that of a loop or that ofa rod (see F igures 1 and 2). Due to current injection at each term inal the chiral chem ical potentials may change their values across them: accordingly we add indices so that $\stackrel{+}{n}$ and $\stackrel{-}{n}$ are on the left of term inal n and change to $\stackrel{+}{n+1}$ and $\stackrel{-}{n+1}$ on the right of the same term inal. Depending on the geom etry for N term inals there will 2N or 2N $\stackrel{-}{2}$ chiral chem ical potentials.

$$_{n}^{+} = X \qquad a_{n}^{p} \text{ eV}_{p} \tag{10}$$

$$_{n} = \overset{X^{p}}{b_{n}^{p}} eV_{p}$$
 (11)

The Ferm ienergy of the LL is taken as the origin of the voltages. These equations simply express an equilibrium condition for the chem ical potentials of the LL with those of the reservoirs. Our point of view is therefore in a sense a therm odynam ical one.

The joint system (LL+ electrodes) is therefore reduced to an isolated LL (i.e. with no electrodes) on which these boundary conditions are imposed. The advantage of such an approach is that it avoids the complications of microscopics. To borrow the language of the renormalization group we view the boundary conditions as characterizing universality classes of the system (LL+ electrodes). Any set of boundary conditions labels a xed point of the joint system and completely determines linear transport as will be shown below.

Since eV_p is the chem ical potential of reservoir p charge conservation results trivially in:

$$1 = \begin{bmatrix} X & a_n^p = X \\ p & b_n^p \end{bmatrix}$$
 (12)

The current in jected at each term inal is simply the dierence between the current circulating on the right of the term inal and the current on the left of it:

$$i_n = K \frac{e}{h}$$
 $_{n+1}^+$ $_{n+1}^+$ $_n^+$ $_n^-$ (13)

Taking into account the boundary conditions eq.(10) leads to:

$$G_{nn} = K \frac{e^2}{h} a_{n+1}^n a_n^n + b_n^n b_{n+1}^n$$
 (14)

$$G_{np} = K \frac{e^2}{h} a_{n+1}^p a_n^p + b_n^p b_{n+1}^p$$
: (15)

It is trivial to check that the following identities are obeyed:

$$X = G_{np} = 0$$
 (16)

$$X^{p}$$
 $G_{pn} = 0$: (17)

The rst identity im plan ents the fact that the origin of potentials is arbitrary (gauge invariance); the second identity is just current conservation.

The requirem ent that 0 nsager-C asim ir relations and positive sem ide niteness of the conductance matrix (this ensures dissipation of energy) be realized evidently puts further constraints on the coe cients a $_{\rm n}^{\rm p}$ and $b_{\rm n}^{\rm p}$ (such as positivity of the diagonal elem ents G $_{\rm nn}$) but we will not use them in this paper.

These boundary conditions can then be straightforwardly generalized to the case of several conducting channels as in carbon nanotubes.

III.A MULTI-TERM INAL MODEL.

We introduce in this part a model derived from one initially proposed by Cham on and Fradkin for the FQHE 17 . The model consists in a chiral Luttinger liquid in contact with N reservoirs through point contacts in the strong coupling limit (no backscattering at the contact) (see Figure 3). We will show that our boundary conditions

form alism can be explicitly derived for this model of strongly correlated electrons; moreover we show that the conductance matrix elements can surprisingly have signs forbidden in the Landauer-Buttiker formalism.

A. Som e useful prelim inaries.

We review rst relevant results for the lagrangian of a chiral LL coupled to a single reservoir 17:

$$L = L_{edge} + L_{reservoir} + L_{tunnel}$$
 (18)

$$L_{\text{edge}} = \frac{1}{4} e_{x}' (e_{t} \quad ue_{x}')$$
 (19)

$$L_{tunnel} = (x)e^{i\frac{e \ v \ t}{h}} + e^{i\frac{e \ v \ t}{h}} (x;t) = (20)$$

The lagrangian for the reservoir is taken to be that of free chiral electrons: the electrons are chiral because free electrons on a half-line are tantam ount to free chiral electrons on a full line. $V = V_{reservoir} V_{edge}^{in}$ is the potential di erence between the reservoir and the incoming edge electrons. The edge electron operator is: $_{edge} = e^{-\frac{1}{2n+1}}$ where $= \frac{1}{2n+1}$ is the Quantum Hall state lling factor.

In the strong coupling lim it, the tunneling current can then be shown to be:

$$i_{\text{tunnel}} = \frac{2}{+1} \frac{e^2}{h} V_{\text{reservoir}} V_{\text{edge}}^{\text{in}}$$
 (21)

which can also be expressed in terms of the chemical potential $V_{\rm edge}^{\rm out}$ after the tunneling event:

$$i_{tunnel} = \frac{e^2}{h} V_{edge}^{out} V_{edge}^{in}$$
 (22)

That expression for the tunneling current is valid at the strong coupling $\,$ xed point (=1): therefore transmission is always perfect with no backscattering at the contact. Away from the xed point (at nite), there would be a contribution due to backscattering which vanishes as $\frac{1}{K}$ V $^{2\,(K-1)}$. In our model we will also work in this ohm ic \lim it of no backscattering.

Cham on and Fradkin then consider N_R such tunnel point contacts, each at the same potential $V_{\rm reservoir}=V_D$ and then N_L similar point contacts at the potential $V_{\rm reservoir}=V_S$. In this way, they modelize a quantum Hall bar at lling with two 2D reservoirs on the left and at the right of the sample, which are connected to the Hall bar through respectively N_L and N_R point contacts. An assumption underlying this model is therefore that the point contacts are incoherent, i.e. each tunneling at each point contacts are incoherent, i.e. each tunneling at each point contacts. The two-term inal conductance can then be easily extracted and depends on the number of contacts N_R and N_L ; in particular the conductance di ers in general from $G_0=\frac{e^2}{b}$:

$$G(N_L;N_R) = \frac{e^2}{h} \frac{1 - \frac{1}{+1}^{N_L} 1 - \frac{1}{+1}^{N_R}}{1 - \frac{1}{+1}^{N_R+N_L}}$$
:

(23)

B.A toy model.

We turn now to our model: it consists in a chiral Luttinger liquid with Luttinger parameter =1=(2n + 1) in a circle geometry with N term inals (Figure 3). That problem is easily solved by observing that it is a generalization of C ham on and Fradkin model found by allowing each of N point contacts to have distinct potentials. The n th term inal has potential $V_{\rm n}$, and due to the current $i_{\rm n}$ which tunnels through it the chemical potential of the chiral LL is raised from $_{\rm n}$ to $_{\rm n+1}$. The associated tunnel lagrangian $L_{\rm tunnel}^{\rm n}$ is exactly similar to $L_{\rm tunnel}$ given above in eq.(18), except for with the location of the tunneling center.

Let us focus on the n the term inal; using equations (21,22); the current i_n is:

$$i_n = \frac{2}{+1} \frac{e}{h} (eV_n _n);$$
 (24)

$$= \frac{e}{h} \left(\begin{array}{cc} & \\ & \\ & \end{array} \right) : \tag{25}$$

This yields the relation:

$$_{n+1} = _{n} + (1) eV_{n}$$
 (26)

where $=\frac{1}{+1}$. Since we work on a circle with N term in hals: $_{N+1}=_{1}$; we then deduce that each potential $_{n}$ can be completely expressed in terms of the potentials of all the term in als:

$$n = \frac{(1 \quad)^{n-1}}{1} \sum_{p=1}^{n} \frac{2^{n}}{p} + \sum_{p=n}^{n} \frac{eV_p}{p} : \quad (27)$$

A coording to eq. (25), the current injected by the n th term inal $i_n = G_{nn}V_n + \bigcup_{p \in n} G_{np}V_p$ yields the conductance matrix:

$$G_{nn} = \frac{e^2}{h} \frac{(1+)(1-N-1)}{1-N}$$
 (28)

$$G_{np} = \frac{e^2}{h} \frac{(1 - 2)^{-d \cdot (n \cdot p) - 1}}{1 - N}; n \in p$$
 (29)

where d(n;p) = n p for n > p, or d(n;p) = N + n p for n < p.

Several points are quite noteworthy:

(1) The boundary conditions described in section 2 are implemented exactly by eq.(27) with the coecients:

$$a_n^p = \frac{(1 \quad)^{-d(n;p)-1}}{1 \quad N}; n \in p$$
 (30)

$$a_{n}^{n} = \frac{(1)^{N-1}}{1}; (31)$$

- (2) In the scattering approach the conductance m atrix is directly related to probabilities of rejection and transmission through: $G_{nn} = \frac{e^2}{h} (1 R_n)$ and $G_{np} = \frac{e^2}{h} T_{np}$. Therefore G_{nn} is a positive number while G_{np} is negative. However in our model G_{np} can be positive depending on the value of d(n;p). More precisely $G_{n;p}$ and $G_{n;p+1}$ have alternating signs: this means that even if electrodes pand p+1 have the same potential currents issued from them are owing in opposite directions to electrode n. This would have been in possible for non-interacting electrons.
- (3) Current conservation and gauge invariance are implemented since: $_p G_{pn} = 0 = _p G_{np}$.
- (4) The quantity $^{\text{h}}_{\text{n},p} V_{\text{n}} V_{\text{p}} G_{\text{np}}$ is always positive, which ensures dissipation of energy.

Proof: It is equivalent to show that $_{n,p}V_nV_p\frac{1}{2}$ ($_{np}+G_{pn}$) 0. It is enough for that purpose to show that the eigenvalues of the matrix $\frac{1}{2}$ ($_{np}+G_{pn}$) are all positive. But $\frac{1}{2}$ ($_{np}+G_{pn}$) is a circulant matrix, i.e. a square matrix whose rows are obtained by displacing the matrix elements of the strow by one column. For a circulant matrix whose strow is $(a_1; ::; a_N)$ the k=1; :::; N eigenvalues are equal to P ($_{nk}$) where $_{nk}=\exp\frac{i2}{N}$ is one of the N th soots of unity and the polynom ial $_{nk}P$ ($_{nk}P$) = $_{nk}P$ ($_{nk}P$) $_{nk}P$ ($_{nk}P$) $_{nk}P$ ($_{nk}P$) is given by:

$$a_{1} = G_{11} = \frac{e^{2}}{h} \frac{(1+)(1-N-1)}{1-N};$$

$$a_{i} = \frac{1}{2} (G_{1i} + G_{i1}) = \frac{e^{2}}{h} \frac{(1-2)}{1-N} \xrightarrow{i=2+-N-i} ;i > 1:$$

Therefore the eigenvalues are given by:

$$P(n_k) = \frac{(1+)^2 (1 \cos \frac{2 k}{N})}{(1+2 2 \cos \frac{2 k}{N})} 0:$$

QED.

O ne eigenvalue vanishes (P $(r_0) = 0$); it corresponds to the eigenvector $(V_1; ::; V_N) = (1; ::; 1)$ which implements gauge invariance (since the origin of voltages is arbitrary no current can ow if all voltages are equal).

- (5) It is easy to check that 0 nsager-C asim ir reciprocity relations are obeyed in this model: $G_{np}(=0) = G_{pn}(=0)$. Since a magnetic eld is present, under time-reversalone must reverse its sign, which implies that is changed into 1=.0 nsager-C asim ir reciprocity then follows immediately from eq. (28-29).)
- (6) An interesting test-case of our model would be an experim ental setup with a FQHE disk for which the number of term in als can be changed easily; what we envision is at rst an experimental conguration with of course few quantum point contacts (at least three in order to observe the alternation of signs of non-diagonal elements of the conductance matrix), which are tuned through a gate voltage, so that the point contacts may be added or removed at will.

IV.BOUNDARY CONDITIONS FOR A LL IN A TWO-TERM IN ALGEOMETRY.

A . B oundary conditions

As an illustration of our form alism we consider the simplest case of a two-term inal geometry with a source and a drain at voltages V_{S} and V_{D} (see Figure 4).

W e take as a boundary condition the relation:

$$+ = A = \frac{eV_S}{eV_D}$$
 (32)

where the matrix A is:

$$A = \begin{array}{cc} a^{S} & a^{D} \\ b^{S} & b^{D} \end{array}$$

and where conservation of the number of particles imposes $a^S + a^D = 1 = b^S + b^D$. The parameter space is therefore two-dimensional. The conductance matrix therefore is:

$$\begin{array}{ccc} G_{SS} & G_{SD} \\ G_{DS} & G_{DD} \end{array} = K \, \frac{e^2}{h} \, (a^S \, b^S) \, \frac{1}{1} \, \frac{1}{1} \quad ; \quad$$

Therefore the two-term inal conductance G $_{2t}=\frac{I}{V_S}=\frac{I_S}{V_D}$ is:

$$G_{2t} = G_{SS} = K \frac{e^2}{h} (a^S b^S) = G_K \text{ det A}$$
 (33)

where the intrinsic conductance of the LL is $G_K = \frac{Ie}{h} = K \frac{e^2}{h}$ (see section 2). Since the two-term inal conductance depends on the di erence ($a^S b^S$) = detA distinct boundary conditions or distinct coupling between the reservoirs and the LL can lead to the same two-term inal conductance value. In contrast a given set of the boundary conditions speci es unambiguously the conductance value. If the two term inals are coupled in a sym metric manner to the LL one has a further condition: $a^S = b^D$. The parameter space is then one-dimensional and $G = K \frac{e^2}{h}$ ($2a^S$ 1).

B . C ontact resistances.

The LL has mean chem ical potential $\overline{}=\frac{++}{2}$; but the reservoirs have potentials eV_S and eV_D. Therefore there is a discontinuity between the chem ical potentials of the reservoirs and the LL. In the standard Landauer-Buttiker picture of the contact resistance, the latter results precisely from such a discontinuity at the boundaries of each reservoir 18 : on a length equal to the inelastic scattering length of each reservoir collisions bring back the energy of each particle coming from the metal to that of the reservoir. In our case, it follows im mediately from the boundary conditions that:

$$eV_{S} = \frac{2 - a^{S} - b^{S}}{2} (eV_{S} - eV_{D}) = \frac{h}{2K} \frac{2 - a^{S} - b^{S}}{(a^{S} - b^{S})} I$$

$$- eV_{D} = \frac{a^{S} + b^{S}}{2} (eV_{S} - eV_{D}) = \frac{h}{2K} \frac{a^{S} + b^{S}}{(a^{S} - b^{S})} I$$

$$(34)$$

which shows that there are two contact resistances:

$$R_{S} = \frac{R_{K}}{2} \frac{2 a^{S} b^{S}}{(a^{S} b^{S})}$$

$$R_{D} = \frac{R_{K}}{2} \frac{(a^{S} + b^{S})}{(a^{S} b^{S})}$$

where the intrinsic resistance of the LL is simply: $R_K=1=G_K$. These expressions also show that the two term in all conductance is obtained from a series addition law of the two contact resistances: $R_S+R_D=\frac{h}{K~e^2}\frac{1}{(a^S-b^S)}=R_{2t}$ (= $\frac{1}{G_{2t}}$). This implies that our boundary conditions incorporate an assumption of incoherence between the contacts. The above two equalities eq.(34) are completely equivalent to the boundary conditions. The two degrees of freedom in the boundary conditions simply reject the fact that there are two contact resistances. In the two terminal geometry we may therefore rewrite the boundary conditions matrix A in terms of the contact resistances:

$$A = \frac{1}{(R_S + R_D)} \qquad \begin{array}{ccc} R_K^c + R_D & R_K^c + R_S \\ R_K^c + R_D & R_K^c + R_S \end{array} ; \quad (35)$$

where we have de ned an intrinsic contact resistance as: R $_{\rm K}^{\,\rm c}$ = $\frac{1}{2G\,_{\rm K}}$ = $\frac{1}{2K\,\,G_{\,0}}$.

Rewriting eq.(34) in terms of the chemical potentials leads to an expression equivalent to the boundary condition expressed by eq.(35):

$$eV_S$$
 = $R_S Ie= R_S G_{2t} (eV_S eV_D)$ (36)
- $eV_D = R_D Ie= R_D G_{2t} (eV_S eV_D)$

C.Cham on and Fradkin m odel.

In the Cham on-Fradkin model a Hallbar has two term in alson its left and on its right 17 . There are N_R (resp. $N_{\rm L}$) point contacts at the right and left term in als. On the upper and lower edges there are chiral Luttinger liquids owing in opposite directions. However the sum of the chiral ham iltonians for each chiral edge is exactly identical to that of a non-chiral LL with parameter K = ...Through our phenom enological form alism, this allows us to describe Cham on and Fradkin microscopic model of a chiralLL as a non-chiralLL but with peculiar boundary conditions. If we make the reasonable assumption that the contact resistances R $_{\rm S}$ and R $_{\rm D}$ depend on N $_{\rm L}$ and N_R respectively (and not on both N_L and N_R), there is a single boundary condition corresponding to Cham on and Fradkin model. Given the two-term inal conductance in eq.(23) we nd the boundary conditions in eq.(35) with:

$$\frac{1}{2R_{D}} = \frac{e^{2}}{h} \frac{1}{1 + 1} \frac{\frac{1}{1} + 1}{1 + \frac{1}{1}}$$
(37)

$$\frac{1}{2R_{S}} = \frac{e^{2}}{h} \frac{1}{1 - \frac{1}{+1}} \frac{N_{L}}{2N_{L}}$$
(38)

This proves that for a non-chiral LL connected to two reservoirs it is perfectly possible theoretically to have non-trivial contact resistances (di erent from $\frac{1}{2G_0}$). The contact resistance $\frac{1}{2G_0}$ is retrieved for N $_R$ = N $_L$ = 1.

D . C om parison w ith earlier theories.

Let us now discuss earlier theories of the two-term inal conductance and show that the dierences between their predicted values of G_{2t} can be completely understood within our boundary condition formalism. The dierences stem from the hypotheses these theories make, in plying dierent boundary conditions and therefore dierent universality classes for the joint system LL+ electrodes.

1. Boundary conditions corresponding to $G_{2t} = K e^2 = h$:

Initially the conductance of the LL was thought to be $G_{2t}=K\ e^2=h$ following the response function calculation³. Such calculation implicitly assumes an inversion symmetry between source and drain. Comparing this conductance value with our computations shows that $R_S=R_D=R_K^c$. Going back to the boundary conditions equations yields the universality class:

$$+ = \begin{array}{c} eV_S \\ eV_D \end{array}$$
 (39)

This allows a physical interpretation of the two-term in al conductance $G_{2t} = K e^2 = h$ for sym etric electrodes: the conductance will be equal to the Luttinger liquid param eter whenever there is an equilibrium between a given reservoir and one of the two chiralities within the LL. In otherwords the current in jected by each electrode is com pletely chiral. Such boundary conditions are realized in the FQHE: one nds indeed a two-term inal conductance $G_{2t} = K e^2 = h$ for a lling fraction K which corresponds to a LL with parameter K . It is also easy to show that eq.(39) is realized in the FQHE for chiral edges. Indeed the chiral currents $i = K \frac{e}{h}$ can be shown by using linear response to be also equal to $i = K \frac{e}{h} S=D$ which then im plies im mediately eq.(39). Such a conductance can also be recovered for a non-chiral LL by using

a Kubo formula where it is assumed that an external eld E $_0$ applied on a length L creates a voltage drop E $_0$ L = eV $_S$ D = eV $_S$ eV $_D$ = $_+$. In our formalism the speci cation of the external electrical eld as E $_0$ = $_-^+$ is then understood as implying an equilibrium between the reservoirs and a chirality of the LL. But m ore generally this needn't be the case and a m ore general linear relation between E $_0$ and $_+$ m ight hold, leading to another value of the two-term inal conductance.

As is clear from our form alism in absence of symetry between source and drain the two term inal conductance value G $_{2t}$ = K e^2 =h can be obtained from any boundary conditions such that R $_S$ + R $_D$ = $2R_K^{\, \rm c}$.

2. Boundary conditions corresponding to $G_{2t} = e^2 = h$:

As we have already mentionned in the introduction many other theoretical approaches predict a non-renormalized conductance value $G_{2t}=G_0=e^2=h$ per channel (these calculations also implicitly assume a mirror symetry between source and drain so that $R_S=R_D$). This shows that $R_S=R_D=\frac{1}{2G_0}$ so that the corresponding boundary conditions can be written in term of the matrix Q [k] de ned in eq.(6) of section 2:

$$^{+}$$
 = Q [K 1] $\stackrel{\text{eV}_{S}}{\text{eV}_{D}}$: (40)

or

$$\begin{array}{lll}
\text{eV}_{S} & = Q \ \text{[K]} & ^{+} & :
\end{array}$$
(41)

Besides for the inhom ogeneous LL m odel (a LL for which the LL parameter K (x) varies with position, K (0 < x < L) = K and K (x) = 1 otherwise) by using continuity equations for the phase elds across the boundaries it can be explicitly shown that²:

$$\begin{array}{ccc} eV_S & = & {\stackrel{0}{\scriptstyle +}} \\ eV_D & \end{array} \qquad ; \qquad \qquad (42)$$

where $^0=\frac{\theta\,H}{\theta\,N^{\,0}}$ are the chiral potentials for non-interacting electrons, that is if K=1 (N 0 is the number of ferm ions at the right or left Ferm i points). But this can be reexpressed in terms of the chiral chemical potentials by noting that the chiral densities are related to the left or right moving ferm ions densities by eq.(5), which results in

$$_{0}^{0} = Q \mathbb{K}]$$
 (43)

U sing the eq.(42,43) leads in m ediatlely to our boundary conditions eq.(41).

For completeness, let us mention several papers which have already developped a narrower boundary conditions

point of view to describe linear transport of LL in a two-term inal geometry. Findich et al. implicitly considered the boundary conditions $\frac{\text{eV}_S}{\text{eV}_D} = \begin{array}{c} 0 \\ 0 \\ 0 \end{array}$ or

$$\begin{array}{ccccc} eV_S & = & ^+ & \mbox{for a LL and for a chiralLL for the} \\ eV_D & & \end{array}$$

3.0 ther boundary conditions?

W ithin our formalism, earlier theories correspond to two particular boundary conditions leading either to $G = K e^2 = h$ or to $G = e^2 = h$. But as discussed in the introduction experimental evidence on carbon nanotubes and quantum wires yield conductance plateaux at values which dier from $G = G_0$ per channel $^4i^7i^5i^9$.

The case of quantum wires fabricated by the cleaved edge overgrowth technique is quite noteworthy: on the one hand evidence points towards a LL physics⁷; on the other hand Landauer scattering approach is used to interpret conductance measurements in⁵. Yet Landauer-Buttiker formalism is invalid in that context of strongly correlated electrons! Our formalism resolves the tension because it includes a theory of linear transport which is independent of Landauer scattering approach, while being applicable to the LL.

W hetherm ore general boundary conditions than those im plicit in earlier theories are realized must be settled by experim ents. But we observe rstly that the Cham on and Fradkin model for two chiral edges can be interpreted as a non-chiralLL connected (albeit in a very peculiarm anner) to two large reservoirs; this model then yields a conductance $G \in G_0$: this implies that at least theoretically there is no grounds for a no-go theorem preventing twoterm in al conductance plateaux at values distinct from the quantum of conductance. Secondly it is noteworthy that in the inhom ogeneous LL model which falls into the eV_S class of boundary condition of current from the reservoirs to the LL is done through a single point contact. But experim entally both quantum wires and carbon nanotubes have a large area in contact with the reservoirs: whether one can safely assume that there is a single tunneling point contact is therefore extremely doubtful. It it then perfectly conceivable that other boundary conditions than eV_D m ay be valid, leading therefore to a conductance $G \in G_0$. The quantum wire or individual single wall carbon nanotubes experiments $\,$ nding conductances unquantized at G $_0$ m ay therefore be explainable using interacting electrons within our form alism .

The variety of boundary conditions re ects simply the nature of the equilibrium achieved between the reservoirs and the LL: the chemical potentials of the charge carriers within the LL (i.e. the chiral chemical potentials) need not be identical with those of the charge reservoirs. Only for sym etric coupling of the electrodes and if $a^S = 1$ does one $\,$ nd that $\,$ eV $_{S}$ = $\,$ $_{+}$ $\,$ and $\,$ eV $_{D}$ = Fisher calculations fall into that class. That boundary condition is natural for the FQHE because it is sensible for the chemical potentials of the reservoirs to be in equilibrium with those of the charge carriers, since the contact region between the FQHE condensate and the reservoirs is large. However as shown microscopically by Cham on et al. 17, if the contact with the reservoirs is not perfect (e.g. a granularity lim its the number of tunneling points), such an equilibrium may not be achieved.

V.TW O-TERM IN AL GEOMETRY WITH AN IMPURITY.

A.New boundary conditions.

We now insert a weak local impurity in the wire:

$$V = u (x) (_{p}^{+} L + hx):$$
 (44)

A current will therefore be backscattered and the potentials need not be identical across the impurity. We use eq.(36) to write boundary conditions in the presence of an impurity:

$$eV_S$$
 $-_L = R_S Ie$ (45)
 $-_R eV_D = R_D Ie$

where the index R=L refers to $_{R=L}$ are the chiral chemical potentials to the right or the left of the impurity and $^-$ is the average between the chiral chemical potentials. To have conditions on the sole chemical potentials it suces then to remark that I = $\frac{K-e}{h}$ ^+_L $_L$ = $\frac{K-e}{h}$ ^+_R , so that:

$$eV_{S} \xrightarrow{L} = R_{S}G_{K} \xrightarrow{L}_{L}$$

$$= R_{D}G_{K} \xrightarrow{R}_{R}$$

$$(46)$$

In spite of these linear relations the chiral chem ical potentials need not depend linearly on the external voltages (there are four chem ical potentials for two linear relations). There is also a non-linear contribution due to the backscattering at the impurity.

B.W hat is the backscattering current?

In the presence of the impurity, some of the current is backscattered. It is usually assumed that the backscattering current is simply the di erence between the current in the absence of impurity and the current in the presence of the impurity. This is only correct for noninteracting systems, but for a LL this will depend on both the conductance $G_{\mbox{\sc 2t}}$ and K . W e must go back to the de nition of the backscattering current as the velocity tim es the density di erence of right-m overs on the left and on the right of the impurity:

$$i_B = u e + k_B + k_B$$
 (47)

This is also equal by charge conservation to: u e $_{
m L}$ $_{
m R}$ with obvious notations. W e can also relate $i_{\mbox{\tiny B}}$ to the chiral chem ical potentials by using the fact that $u \stackrel{+}{}_{L} = \frac{K}{h} \stackrel{+}{}_{L}$ (with sim ilar relations for the rality and for the potentials to the right of the im purity). Therefore:

$$i_B = \frac{K \ e}{h} \quad {}_L^+ \quad {}_R^+ = \frac{K \ e}{h} \quad {}_L \quad {}_R :$$
 (48)

Using the new boundary conditions (46):

$$eV_S$$
 $eV_D = \frac{}{}_R + R_D Ie + \frac{}{}_L + R_S Ie$
= $R_K i_B e + (R_S + R_D) Ie$

where $R_K = h=K e^2$. This can be recast as:

$$I = I_0 \qquad \frac{R_K}{R_S + R_D} i_B$$

$$\in I_0 \qquad i_B$$
(49)

w here

$$I_0 = \frac{eV_S - eV_D}{e(R_S + R_D)}$$
 (50)

is the current in the absence of an impurity and is therefore also the saturation current, i.e. the maxim alcurrent which can be reached when one goes to large voltages. The fact that $i_B \in I_0$ I contrary to the naive expectation stems from the contact resistances: the dierence between i_B and I I_0 is akin to the dierence between a two-tem inal and a four-term inal measurement. I_0 takes into account the resistance at the contacts while in is more intrinsic and measures the net current wich is backscattered locally at the impurity.

VI.SHOT NOISE IN A TWO-TERM IN A L GEOMETRY.

W hat are the elementary excitations of the LL? The textbook answer is that there are two kinds of excitations: (1) bosonic density uctuations (plasmons); (2) zero modes ladder operators which change the number

of particles at each Ferm ipoint but have no dynamics3. It is seldom remarked that such a description of the excitations found for the LL through the bosonization m ethod is also valid for free electrons. W hat this m eans is that for free electrons there are two equivalent manners of describing the elementary excitations (corresponding to two basis of eigenstates): (1) the usual manner, in terms of charged quasiparticles (the electron and the hole); (2) and the one provided by bosonization, which yields bosonic density uctuations and ladder operators. The two descriptions diermarkedly in that the second involves charged excitations which have no dispersion, while in the rst the charge dynamics is described by the usual quasiparticles.

For the LL it can be shown that exactly in the same manner there exists a basis of charged quasiparticles. However instead of the Landau quasiparticle one nds fractional elem entary excitations, which may even carry irrational charges. In particular the particle-hole continuum of Ferm i liquid theory is replaced by a quasiparticlequasihole continuum of excitations which are the analogs of Laughlin quasiparticles 16. For the chiral LL (the edge states of the FQHE) they have been detected through shot noise. In the case of the non-chiral LL a marked di erence is that such shot noise experim ents would allow to detect irrational charges (the FQ HE lling fraction which is a rational number is replaced by the LL pa-

ram eter K).

Present theories of shot noise can be roughly separated into two camps: A Kane, Fisher, Balents et al. 22;23 predict a Fano factor equals to Ke. This is commonly interpreted as the proof that excitations of charge K e are responsible for the noise. This calculation however makes no explicit modelization of the reservoirs; B Ponom arenko et al., Egger et al.24 work with the inhom ogeneous LL (two term inalgeom etry which models the reservoirs as 1D Ferm i liquids on a half-line) and nd a Fano factor or excitations of charge equals to e. W e note that B lanter and Buttiker have argued against this last result by noting that the shot noise should not depend on the reservoirs since this is a measure of the charge backscattered locally by the impurity. We discuss now these two sets of theories: A we apply our boundary conditions form alism to the shot noise theory of K ane and Fisher; B for the inhom ogeneous LL we discuss the meaning of their result in the light of the identities derived in the previous section.

A . K ane-F isher approach

The shot noise through a weak impurity in a LL was rst computed by K ane and Fisher (for the edge states of the FQHE and before the actual proof that there exists also Laughlin quasiparticles in the LL) by using the Keldysh formalism applied to an e ective lagrangian found by integrating out the degrees of freedom away

from an unique impurity (is the standard LL phase eld at the location of the impurity)²²:

$$L = \frac{1}{2K} \sum_{n=1}^{X} j!_{n} jj (i!_{n})^{2}_{j} + d v cos(2^{p} - ()); (51)$$

A lthough initially intended for the edge states of the FQHE the calculation is also valid for the non-chiralLL. K ane and Fisher nd that the current and the noise are given respectively by:

$$I = K \frac{e^2}{h} \frac{da}{dt} V ; (52)$$

$$S_{I} = K e K \frac{e^{2}}{h} \frac{da}{dt} I$$
 (53)

where $V = \frac{h}{e} v \sin (2^{p} - (+ K a) , w ith a source term ja added to the lagrangian. K ane and F isher assumed that$

$$e^{\frac{\mathrm{da}}{\mathrm{dt}}} = e(V_{\mathrm{S}} \quad V_{\mathrm{D}}): \tag{54}$$

In the absence of impurity V = 0, eq.(52) leads to

$$I_0 = K \frac{e^2}{h} \frac{da}{dt}; (55)$$

on the other hand according to eq.(8), $I_0 = K_{\frac{e}{h}}(t_+)$, together with eq. (54) this then in plies that $e(V_S V_D) = t_+$). Therefore within K ane-Fisher approach and assuming eq. (54) the \two term inal" conductance value is $G_{2t} = K_{e}^2 = h$ in the absence of an impurity. Moreover as discussed in section 4.4 (assuming symmetric coupling to source and drain) this calculation falls into the class of boundary conditions which

correspond to
$$^{+}$$
 = $\overset{\text{ev}_{S}}{\text{eV}_{D}}$, i.e. equilibrium of

the reservoirs chem ical potentials with those of the LL. In order to obtain values of the conductance di erent from K e^2 =h, it is su cient to change the previous assum ption eq. (54): other classes of boundary conditions are found simply by assuming that the response of the LL is totally driven by the values of the chiral chemical potentials (the chemical potentials of the charge carriers of the LL) in the absence of an impurity, and not by the reservoirs potentials (since there is no reason why they should be equal). We therefore modify eq.(54) into:

$$e\frac{da}{dt} = {}_{+} (56)$$

$$= \frac{R_K}{R_S + R_D} e(V_S \quad V_D) \tag{57}$$

where in the second line the boundary conditions (35) in the absence of impurity have been used. Eq. (57) together with eq. (55) then lead to the value of the \two-term inal" conductance that we obtained with our

approach in section 4 for the same boundary conditions, namely $G_{2t} = 1 = \langle R_S + R_D \rangle$.

So far we have shown that by assuming the source term de nition Eq. (57) instead of Eq. (54) it is possible to adapt K ane-Fisher calculations to reproduce the various boundary conditions in the absence of impurity.

We can now reconsider K ane and F isher's calculations for the shot noise, i.e. in the presence of an impurity in the bulk of the LL. M ore precisely we express now the shot noise as a function of either I_0 I (the deviation to the saturation current) or as a function of the backscattering current $i_{\rm B}$, for the various boundary conditions. A coording to eq. (55) and eq. (53) we always have independently of the boundary condition chosen:

$$S_{T} = K e(I_{0} \quad I) :$$
 (58)

Therefore, using eq. (49) $I = I_0 = \frac{R_K}{R_S + R_D} i_B = I_0 = \frac{G_{2L}}{G_K} i_B$ the last equality is also recast as:

$$S_{I} = \frac{G_{2t}}{G_{0}} e i_{B}; \qquad (59)$$

where G $_{2t}$ is the two term inal conductance that re ects the contact resistances in the absence of the impurity. The shot noise Fano factorm ight therefore appear to depend on whether one refers to the backscattering current i_B or to I_0 . I, the deviation to the saturation current. But since $S_{\rm I}$ is the uctuation of the current I, the physical shot noise charge must be measured with respect to the current I and not with respect to the current I and not with respect to i_B . The shot noise charge is therefore $\frac{s_{\rm I}}{I_0-I}=K$ e, independently of the boundary condition realized in the system and is not equal to $\frac{s_{\rm I}}{i_n}$.

At any rate what is directly measured is always I or $I_0: i_B$ is only indirectly accessible through for instance eq. (49).

In sum m ary, within the K ane and F isher calculation by the K eldysh m ethod, it is therefore possible to have (i) an ohm ic conductance distinct from K e^2 =h and (ii) a shot noise charge equal to K e independently on the value of the ohm ic conductance.

B . Inhom ogeneous m odel approach

The role of the reservoirs on the measure of the shot noise of a LL was exam ined in two papers 24 , which make calculations on the inhom ogeneous LL model for which the boundary condition is $\frac{\text{eV}_S}{\text{eV}_D} = \text{Q K } \text{]} \quad \text{as discussed in section 4.4.} \text{ They both not that S}_I = \text{e}(I_0 \quad I) \text{ with a conductance G}_{2t} = \text{G}_0 \quad \text{. It is interesting to remark that the equation S}_I = \text{e}(I_0 \quad I) \text{ can be recasted in terms of the backscattering current noise as:}$

$$S_{i_B} = K e i_B;$$

 $since I_0$ $I = i_B = K$ when $G_{2t} = G_0$.

The result of Ponom arenko et al. and Egger et al. acquires then the following interpretation: the charge K e is not found in the shot noise for the total current in the LL because it is really the correlations of the backscattering current which should be measured. Since the impurity backscatters charge K e Laughlin quasiparticles, the backscattering current correlations must contain the information on the charge backscattered by the impurity.

This is in disagreem ent with K ane and F isher theory even when this last theory is modi ed by our boundary conditions form alism in order to reproduce the situation $G_{2t}=G_0$. We are unable as yet to explain the discrepancy between the two approaches.

Lastly, we note that taking the relation $S_{i_B}=Kei_B$ as a starting point, this then according to our form alism leads inevitably to $S_I=\frac{G_{2L}}{G_0}$ e (I_0-I) . An experimental test of this last suggestion would require an independant measurement of K and i_B . In FQHE such independant measurement is possible because the two chiralities of the elective LL are physically well separated and a direct measure of K is then possible through the Hall conductance. In contrast to the FQHE, i_B is not experimentally measureable in Carbon nanotubes: this then means in turn that even though $S_{i_B}=Kei_B$ the charge of Laughlin quasiparticles in a non-chiral LL is not directly measurable through shot noise in a two-term inal geometry.

Shot noise experim ents will hopefully settle the issue. In this respect some experiments on carbon nanotubes are in progress 26 .

VII.CONCLUSIONS.

We proposed in this paper a new form alism which modelizes the pint system LL+ electrodes as a single LL with no electrodes but subjected to boundary conditions on its chiral chem ical potentials. We were able to show in a solvable toy-model that such boundary conditions can indeed be derived explicitly. That model is quite remarkable because the conductance matrix of the LL in contact with an arbitrary number of term in als can be computed; it is found that the probabilistic scattering approach fails: it would lead to negative probabilities for the transm ission of electrons. The obvious advantage of our form alism is that it avoids discussion of the detailed microscopics of a system, but yields a classication of the pint system LL+ electrodes and then makes precise predictions for the transport. In particular the Landauer-Buttiker view of the contact resistance as resulting from a mism atch between chem ical potentials is recovered; if the charge backscattered by an impurity in a LL is $\frac{\mathbf{S}_{1_B}}{\mathbf{i}_B}$ we nd that the shot noise of the total current does not allow a measure of the fractional charge K e of Laughlin particles in a LL.

It is easy to generalize our form alism to the case of several channels: (i) several conducting channels as in

carbon nanotubes; (ii) spin transport: this arises with ferrom agnetic reservoirs; (iii) application of a magnetic eld on the LL, which breaks the spin-charge separation.

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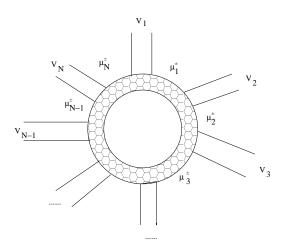
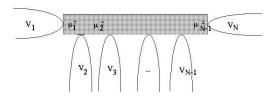


FIG.1. LL connected to many electrodes in a loop geometry. V_n is the potential of electrode n. $_n$ are the chiral chemical potential on the left of electrode n. Due to current injection at each term in all the chiral chemical potentials machange their values across them: accordingly $_n$ on the left of term in all n is changed to $_{n+1}$ on the right of the sam term in al.



 ${\tt FIG.2.}$ Same as ${\tt Fig. 1}$ but for LL connected to many electrodes in a rod geom etry.

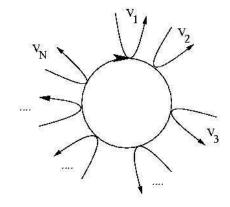


FIG.3. Model of a chiral LL connected to many chiral electrodes in a loop geom etry.

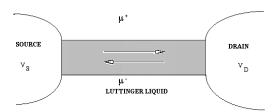


FIG. 4. LL in a two term in als geom etry.